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Low Power NPN Silicon Transistor

Qualified per MIL-PRF-19500/391

Qualified Levels:
JAN, JANTX,
JANTXV, and JANS

DESCRIPTION

This 2N3700 NPN transistor comes in a hermetically sealed metal TO-18 package and is military qualified for high-reliability applications.

Important: For the latest information, visit our website <http://www.microsemi.com>.

FEATURES

- JEDEC registered 2N3700 number.
- JAN, JANTX, JANTXV and JANS qualifications are available per MIL-PRF-19500/391.
- Rad hard levels are also available per MIL-PRF-19500/391. (See RHA datasheet for [JANS 2N3700](#).)
- RoHS compliant versions available (commercial grade only).

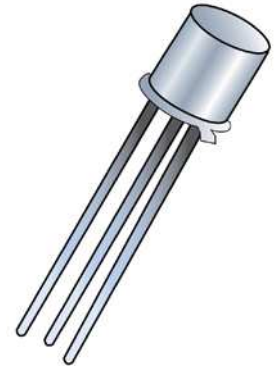
APPLICATIONS / BENEFITS

- Leaded, hermetically sealed TO-18 package.
- Lightweight.
- Low power.
- Military and other high-reliability applications.

MAXIMUM RATINGS @ T_A = +25 °C unless otherwise noted.


Parameters/Test Conditions	Symbol	Value	Unit
Junction and Storage Temperature	T _J and T _{STG}	-65 to +200	°C
Thermal Impedance Junction-to-Ambient	R _{θJA}	325	°C/W
Thermal Impedance Junction-to-Case	R _{θJC}	150	°C/W
Collector-Emitter Voltage	V _{CEO}	80	V
Collector-Base Voltage	V _{CBO}	140	V
Emitter-Base Voltage	V _{EBO}	7.0	V
Collector Current	I _C	1.0	A
Total Power Dissipation:	@ T _A = +25 °C ⁽¹⁾	0.5	W
	@ T _C = +25 °C ⁽²⁾	1.0	


- Notes:**
1. Derate linearly 2.85 mW/°C for T_A ≥ +25 °C.
 2. Derate linearly 10.3 mW/°C for T_C ≥ +25 °C.





TO-18 (TO-206AA) Package

Also available in:

UB package
(surface mount)
 [2N3700UB](#)

TO-39 (TO-205AD)
(leaded)
 [2N3019](#)

TO-5 package
(leaded)
 [2N3019S](#)

TO-46 (TO-206AB)
(leaded)
 [2N3057A](#)

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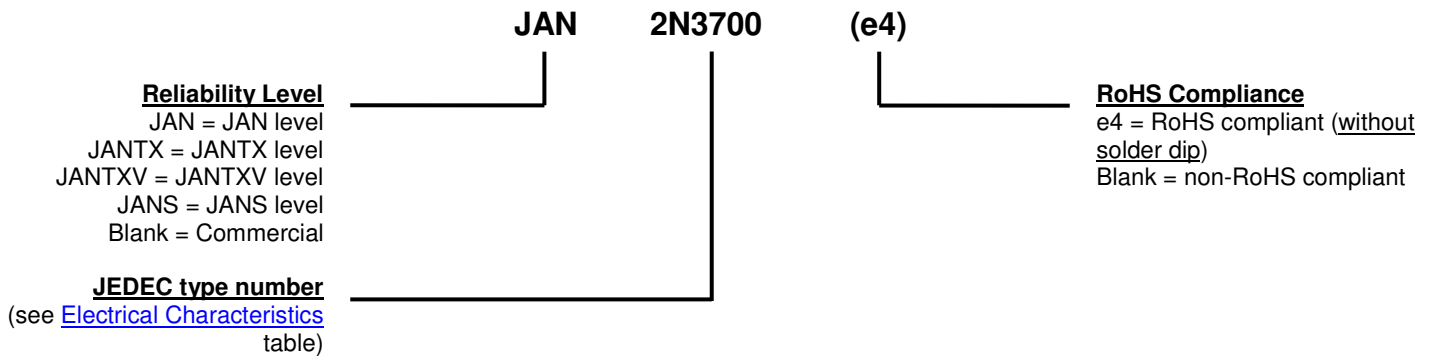
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MECHANICAL and PACKAGING

- CASE: Hermetically sealed, nickel plated kovar base, nickel cap.
- TERMINALS: Gold plate over nickel, kovar for JANS. Gold plate over nickel, kovar, solder dipped for JAN, JANTX, and JANTXV.
- MARKING: Part number, date code, manufacturer's ID.
- WEIGHT: Approximately 0.3 grams.
- See [Package Dimensions](#) on last page.

PART NOMENCLATURE

SYMBOLS & DEFINITIONS

Symbol	Definition
f	Frequency
I_B	Base current (dc)
I_E	Emitter current (dc)
T_A	Ambient temperature
T_C	Case temperature
V_{CB}	Collector to base voltage (dc)
V_{CE}	Collector to emitter voltage (dc)
V_{EB}	Emitter to base voltage (dc)

ELECTRICAL CHARACTERISTICS @ $T_A = +25\text{ }^\circ\text{C}$ unless otherwise noted

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage $I_C = 30\text{ mA}$	$V_{(BR)CEO}$	80		V
Collector-Base Cutoff Current $V_{CB} = 140\text{ V}$	I_{CBO}		10	μA
Emitter-Base Cutoff Current $V_{EB} = 7\text{ V}$	I_{EBO1}		10	μA
Collector-Emitter Cutoff Current $V_{CE} = 90\text{ V}$	I_{CES}		10	nA
Emitter-Base Cutoff Current $V_{EB} = 5.0\text{ V}$	I_{EBO2}		10	nA
ON CHARACTERISTICS				
Forward-Current Transfer Ratio $I_C = 150\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 0.1\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 10\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 500\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 1.0\text{ A}, V_{CE} = 10\text{ V}$	h_{FE}	100 50 90 50 15	300 300 300	
Collector-Emitter Saturation Voltage $I_C = 150\text{ mA}, I_B = 15\text{ mA}$ $I_C = 500\text{ mA}, I_B = 50\text{ mA}$	$V_{CE(sat)}$		0.2 0.5	V
Base-Emitter Saturation Voltage $I_C = 150\text{ mA}, I_B = 15\text{ mA}$	$V_{BE(sat)}$		1.1	V

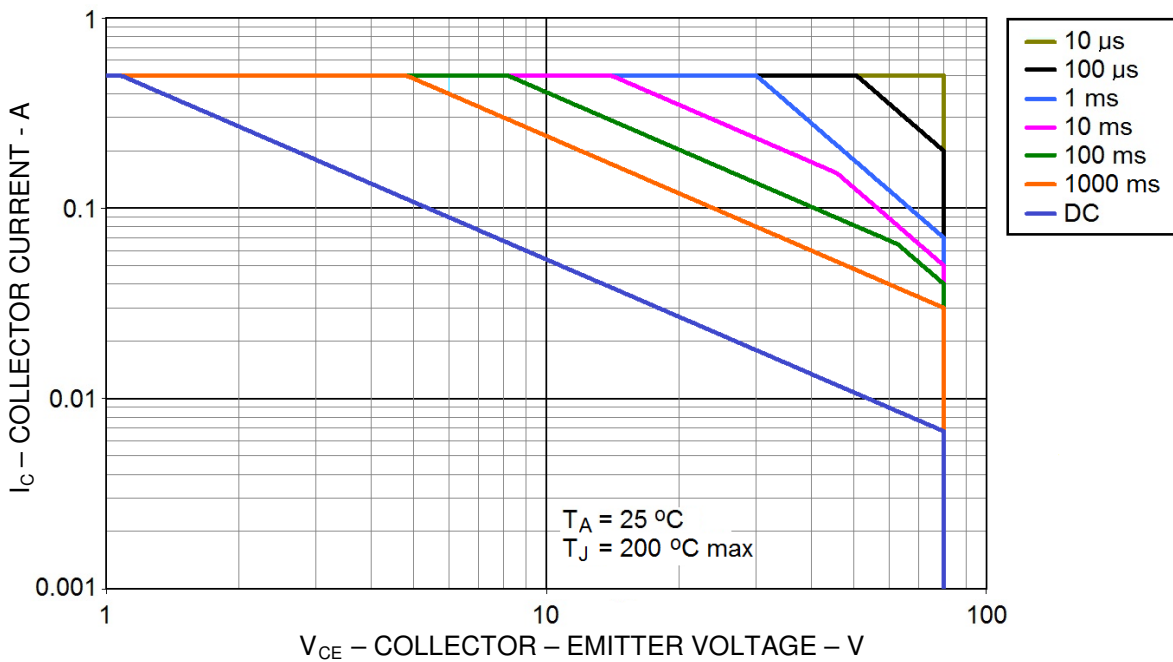
DYNAMIC CHARACTERISTICS

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Small-Signal Short-Circuit Forward Current Transfer Ratio $I_C = 1.0\text{ mA}, V_{CE} = 5.0\text{ V}, f = 1.0\text{ kHz}$	h_{fe}	80	400	
Magnitude of Small-Signal Short-Circuit Forward Current Transfer Ratio $I_C = 50\text{ mA}, V_{CE} = 10\text{ V}, f = 20\text{ MHz}$	$ h_{fe} $	5.0	20	
Output Capacitance $V_{CB} = 10\text{ V}, I_E = 0, 100\text{ kHz} \leq f \leq 1.0\text{ MHz}$	C_{obo}		12	pF
Input Capacitance $V_{EB} = 0.5\text{ V}, I_C = 0, 100\text{ kHz} \leq f \leq 1.0\text{ MHz}$	C_{ibo}		60	pF

ELECTRICAL CHARACTERISTICS @ $T_A = +25\text{ }^\circ\text{C}$ unless otherwise noted (continued)
SAFE OPERATION AREA (See SOA graph below and [MIL-STD-750, method 3053](#))

DC Tests
 $T_C = 25\text{ }^\circ\text{C}$, 1 cycle, $t = 10\text{ ms}$

Test 1 2N3700	$V_{CE} = 10\text{ V}$ $I_C = 180\text{ mA}$
Test 2 2N3700	$V_{CE} = 40\text{ V}$ $I_C = 45\text{ mA}$
Test 3 2N3700	$V_{CE} = 80\text{ V}$ $I_C = 22.5\text{ mA}$

 (1) Pulse Test: Pulse Width = $300\text{ }\mu\text{s}$, duty cycle $\leq 2.0\%$.

Maximum Safe Operating Area @ $T_A = 25\text{ }^\circ\text{C}$

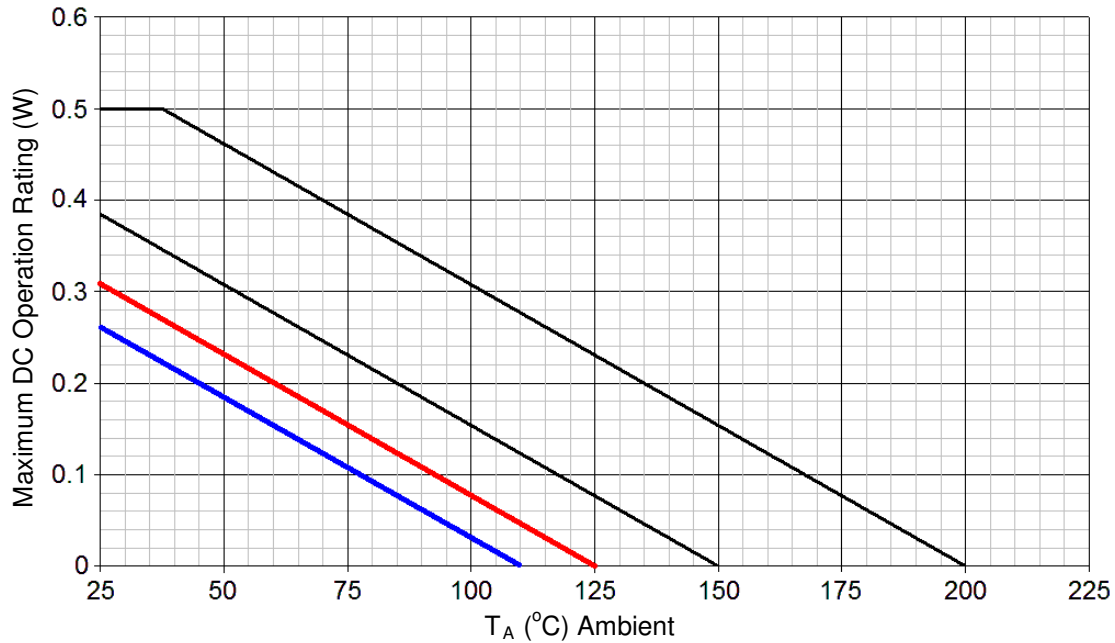
GRAPHS


FIGURE 1
Temperature-Power Derating (R_{θJA})
 Leads = 0.125 inch (3.175mm)

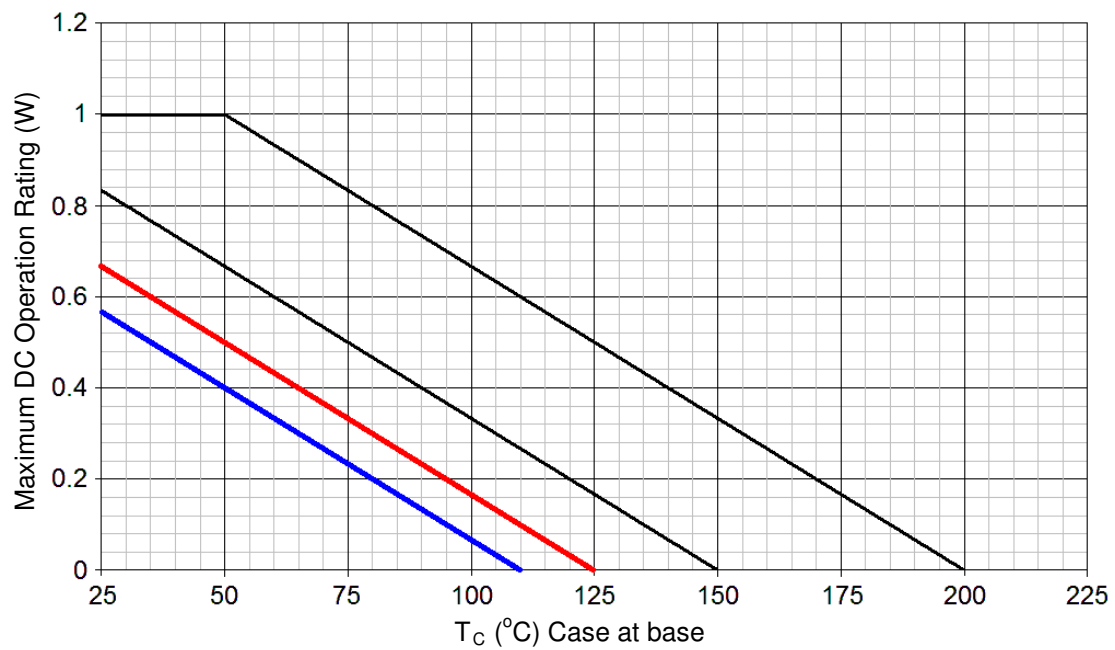
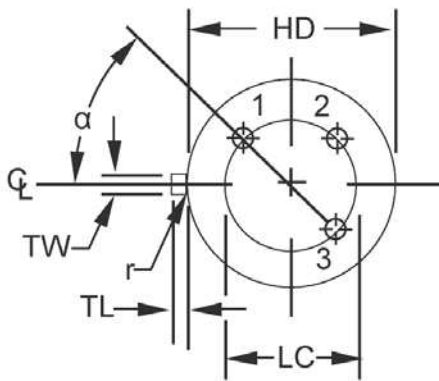
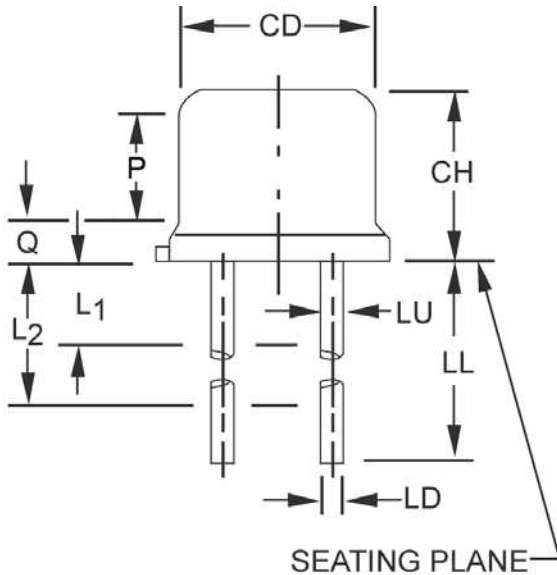


FIGURE 2
Temperature-Power Derating (R_{θJC})

PACKAGE DIMENSIONS


Symbol	Dimensions				Note
	Inch		Millimeters		
	Min	Max	Min	Max	
CD	0.178	0.195	4.52	4.95	
CH	0.170	0.210	4.32	5.33	
HD	0.209	0.230	5.31	5.84	
LC	0.100 TP		2.54 TP		6
LD	0.016	0.021	0.41	0.53	7,8
LL	0.500	0.750	12.70	19.05	7,8
LU	0.016	0.019	0.41	0.48	7,8
L1	-	0.050	-	1.27	7,8
L2	0.250	-	6.35	-	7,8
P	0.100	-	2.54	-	
Q	-	0.030	-	0.76	5
TL	0.028	0.048	0.71	1.22	3,4
TW	0.036	0.046	0.91	1.17	3
r	-	0.010	-	0.25	10
α	45° TP		45° TP		6
1, 2, 9, 11, 12					

NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. Beyond r (radius) maximum, TH shall be held for a minimum length of .011 inch (0.28 mm).
4. Dimension TL measured from maximum HD.
5. Body contour optional within zone defined by HD, CD, and Q.
6. Leads at gauge plane .054 +.001 -.000 inch (1.37 +0.03 -0.00 mm) below seating plane shall be within .007 inch (0.18 mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC. This device may be measured by direct methods.
7. Dimension LU applies between L₁ and L₂. Dimension LD applies between L₂ and LL minimum. Diameter is uncontrolled in L₁ and beyond LL minimum.
8. All three leads.
9. The collector shall be internally connected to the case.
10. Dimension r (radius) applies to both inside corners of tab.
11. In accordance with ASME Y14.5M, diameters are equivalent to Φx symbology.
12. Lead 1 = emitter, lead 2 = base, lead 3 = collector.